



Bipolar PNP Bare Die – BTP6005

Part Description

The BTP6005 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6005

Key Parameters:

- VCBO = -40V
- VCEO = -32V
- VEBO = -5V
- hFE = 68-400 @ VCE = -3V, IC = -0.1A
- VCE(Sat) = -0.4V @ IC = -0.5A, IB = -50mA
- fT = 100 MHz @ VCE = -5V, IE = 0A
- COBO = 25pF @ VCB = -10V

Features

High VEBO. Designed to provide performance equivalent to ROHM 2SA934

Die Size (Unawn)

650µm X 650µm, 26 Mils X 26 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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